

/ Descriptions

TO-252 SiC

SiC Schottky Barrier Diode in a TO-252 Plastic Package.

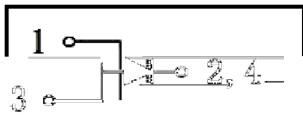
/ Features

Low power loss, high efficiency, HF Product.

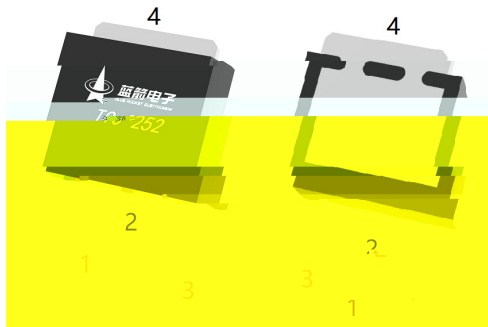
/ Applications

For high frequency, high voltage, high current rectifier diode, freewheeling diode

/ Equivalent Circuit



/ Pinning



PIN1 3 Anode PIN 2 4 Cathode

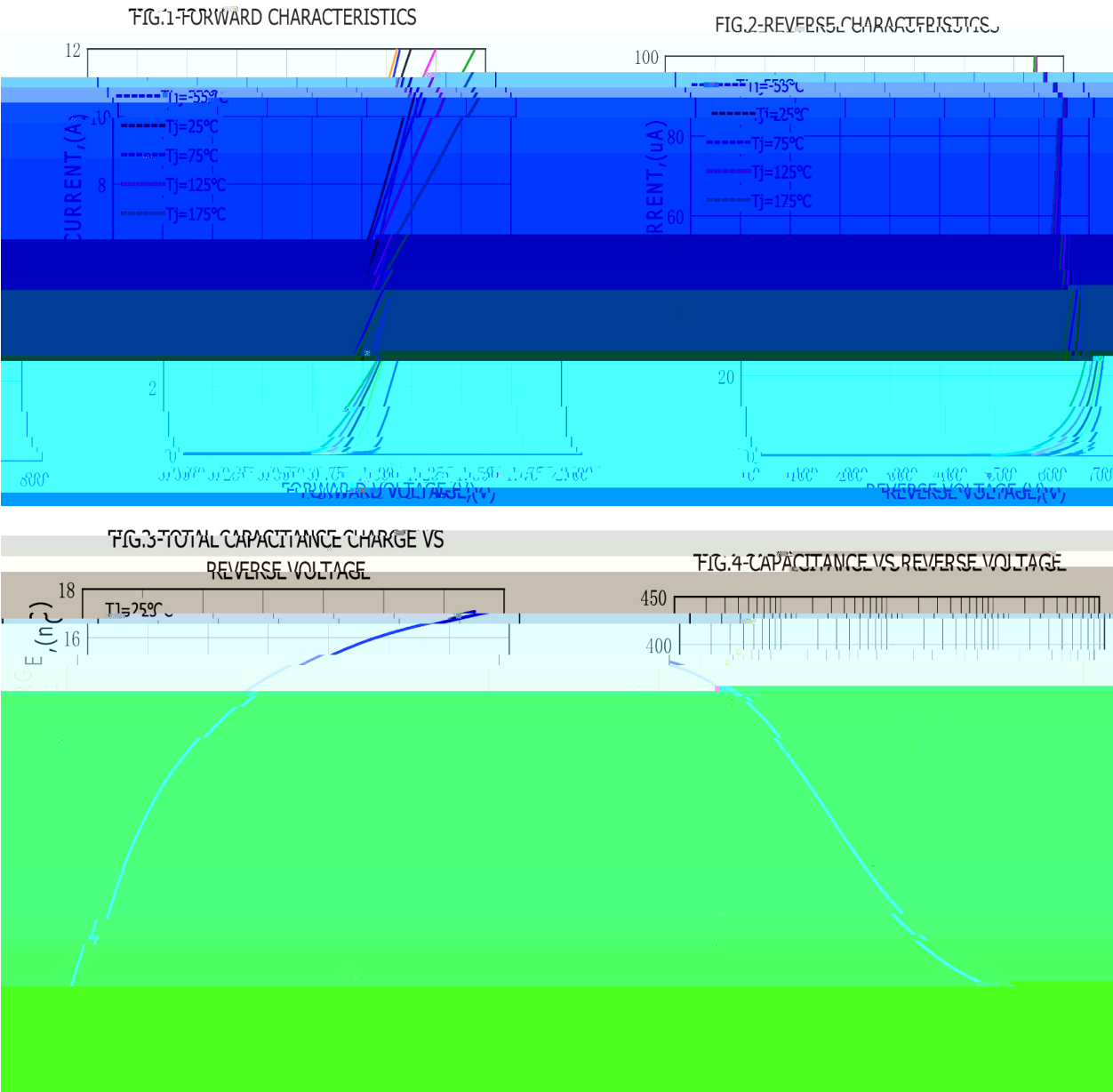
/ Marking

See Marking Instructions.

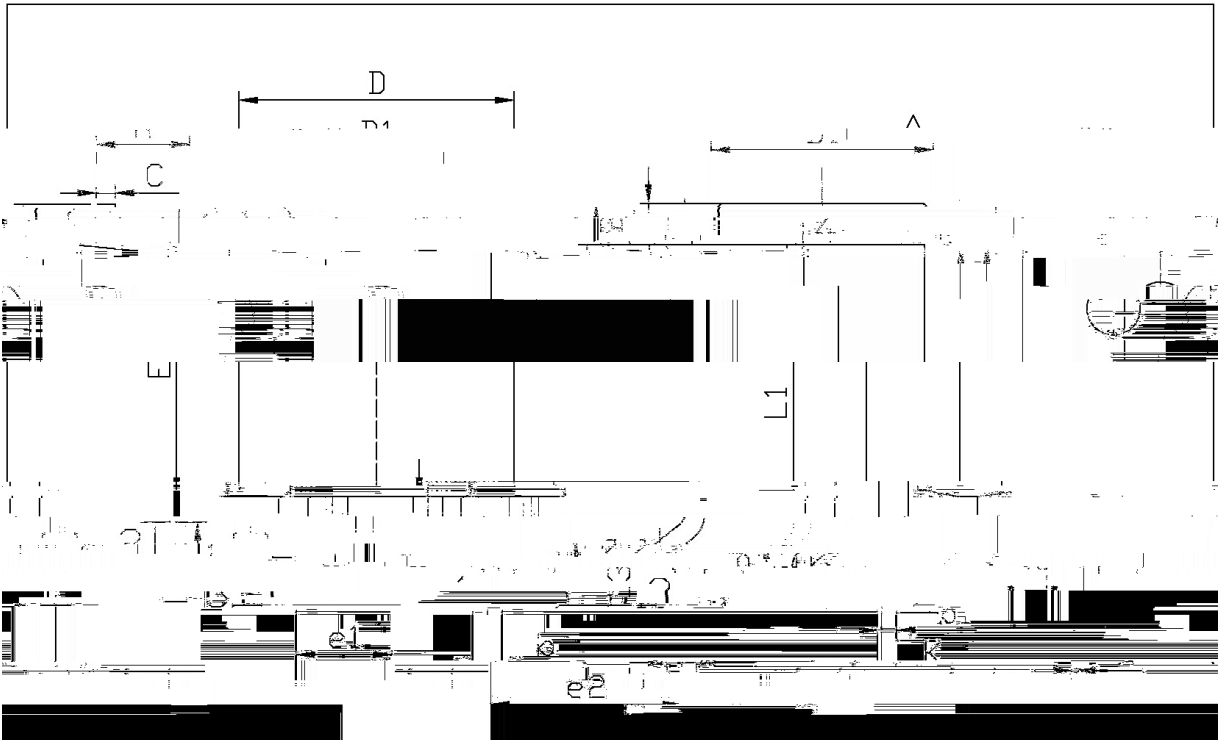
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	650	V
Maximum RMS Voltage	V_{RMS}	455	V
Maximum DC blocking Voltage	V_{DC}	650	V
Continuous Forward Current, $T_C=150$	I_F	6	A
Peak forward surge current, $t_p=8.3ms$	I_{FSM}	52	A
Total power dissipation	P_D	53	W
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	2.8	/W
Operation Junction Temperature and Storage Temperature	T_J, T_{STG}	-55~+175	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
-----------	--------	-----------------	-----	-----	-----	------

/ Electrical Characteristic Curve



/ Package Dimensions



单位: mm

Max	Symbol	Min	Max	Symbol	Min
6.25	A	2.20	2.40	F	5.95
1.6	B	0.50	0.75	4.43	E
1.61	C	0.45	0.55	9.45	L
0.66	D	0.55	0.65	0.75	e1
0.66	D1	0.55	0.65	0.75	e2
5.16	L	5.56	6.45	K	0.009

12-252

